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SWITCHING POWER SOURCE

TECHNICAL FIELD

This invention relates to a switching power source, in particular, of the type wherein a primary side of a transformer can serve to accurately and reliably detect an electrical load condition on a secondary side to improve the conversion efficiency.

BACKGROUND OF THE INVENTION

A known switching power source of self-induced flyback type such as RCC (ringing choke converter) is defective in that it increases on-off switching frequency of a switching element when an electric load becomes light because the on-period of the switching element becomes shorter with the shorter period of producing flyback voltage on a secondary winding of a transformer. A typical on-off switching frequency or oscillation frequency of switching element generally ranges from 30 to 70 kHz under the maximum load and from 200 to 400 kHz under the minimum load. Thus, with the lighter load, the number of times the switching element is turned on and off is increased, resulting in augmentation of switching loss and reduction of conversion efficiency during the light load period. Accordingly, even a switching power source of 85 % conversion efficiency under the maximum load may sometimes reduce the conversion efficiency equal to or less than 10 % under the minimum load.

A typical switching power source of PWM (pulse width modulation) flyback type does not change the switching loss of switching element because

oscillation frequency is constant either under the minimum load such as stand-by state or under the maximum load such as normal state. However, as electric loss other than switching loss is decreased during the light load period, switching loss occupies a major proportion, reducing the conversion efficiency.

To overcome the foregoing defects, Japanese Patent Disclosure No. 9-140128 demonstrates a switching power source which, as shown in Figure 26, comprises a microcomputer 108 provided on a secondary side of a transformer 106 for detecting or controlling operation of a device; and a delivery circuit 109 for transporting control signals from microcomputer 108 to a primary side of transformer 106 to control oscillation frequency of the power source by microcomputer 108 during the stand-by mode. A switch element 101 is connected to a primary winding of transformer 106 to control electric current flow through the primary winding. A drive circuit 102 produces drive signals to switch element 101 which is turned on when electric voltage applied on a control terminal of switch element 101 reaches a threshold level. A drive controller 103 serves to control on-time of switch element 101 to stabilize the output voltage from secondary side. A secondary rectifying and smoothing circuit 104 is connected to a secondary winding of transformer 106, and a primary rectifying and smoothing circuit 105 is connected to a primary auxiliary winding of transformer 106. Transformer 106 functions to electrically insulate between primary and secondary sides, and simultaneously, forms an electro-magnetic coupling to convert a primary input electric voltage into a desired secondary output voltage. A detector 107 picks out a secondary output voltage generated from secondary rectifying and smoothing circuit 104. This switching power source is advantageous because it reduces switching loss in the stand-by mode or during the light load period,

thereby resulting in improved conversion efficiency, however disadvantageous because it requires increased number of required components that causes rise in cost of manufacture. Also, it is actually impossible to apply the switching power source to AC adaptors for small electronic devices such as mobile phones or personal handy phone systems or portable personal computers because the power source involves a large-scale addresser such as a microcomputer.

In the meantime, to detect electrical load condition on the secondary side, the load current has to be detected on the second side and then transmitted to the primary side. Alternatively, a microcomputer has to be provided in the secondary side to deliver command signals from such a microcomputer to the primary side. However, in any event, these arrangements have a drawback of increase in number of required components for assembly. Accordingly, it would be necessary for the power source to accurately discern the secondary load condition directly from the primary side in order to minimize number of required components. Techniques for appreciating the secondary load condition on the primary side include measurements of: switching current flow through a switching element; voltage feedback signals from secondary side; and time period of flyback voltage generated through a winding of transformer. The first technique for measuring switching current flow through switching element is generally realized in many cases as an over-current protector (OCP) which may comprise a resistor for detecting electric current therethrough and a comparator connected to the resistor. This technique, however, unfavorably may cause capacitive short-circuit over-current to flow through the switching element at the moment of turning it on as shown in Figure 27 due to a parasitic capacitance formed by an inherent structure in the switching

element; a snubber circuit (such as a capacitor) connected between two electrodes of the switching element for reduction of noise or another snubber circuit connected between windings of transformer to reduce noise and protect the switching element. The capacitative short-circuit over-current disturbs the accurate detection of secondary load condition because the over-current cannot be determined only by the secondary load condition, and moreover, a peak value of the over-current may be elevated over a peak value of a secondary load current during the light load period. For that reason, without accomplishing any purpose for detecting the secondary load condition, namely, light or heavy load condition, the foregoing current detecting resistor is generally used as a protective circuit against over-current for restricting excessive switching current in case of preventing some malfunction of the switching element (for example, over-load condition by a damaged secondary circuit or uncontrolled condition by a damaged control system). Accordingly, such a prior art switching power source makes it very difficult to exactly detect the secondary load condition on the primary side with minimum number of required components in order to select an optimal oscillation operation based on the detection result on the primary side and thereby improve the conversion efficiency of the power source.

Hence, an object of the present invention is to provide a switching power source capable of exactly detecting a secondary load condition on a primary side of a transformer for improvement of the conversion efficiency.

SUMMARY OF THE INVENTION

The switching power source according to the present invention comprises a DC power source (1); a primary winding (2a) of a transformer (2)

and a switching element (3) connected in series to the DC power source (1); a current detector (9) for acquiring electric current (I_D) flowing through the primary winding (2a) of the transformer (2) or the switching element (3); a rectifying smoother (6) connected to a secondary winding (2b) of the transformer (2) for generating DC output voltage (V_{OUT}); and a control circuit (8) for supplying the switching element (3) with drive signals (V_G) to turn the switching element (3) on and off so as to keep the DC output voltage (V_{OUT}) on a substantially constant level. The control circuit (8) comprises a current comparator (27) for comparing a voltage level of signals acquired by the current detector (9) with a reference voltage level (V_{DT}) to produce detection signals (V_{CP}) of first or second level (L or H); an edge detector (28a) for sensing an edge of drive signal (V_G) supplied to a control terminal of the switching element (3) during the period of transition from turning on to off of the switching element (3); and a decision means (28b) for receiving a current detection signal (V_{CP}) from the current comparator (27) to produce an output signal (V_{LD}) when the edge detector (28a) catches an edge of drive signal (V_G); wherein the decision means (28b) produces the different output signals (V_{LD}) of respectively first and second voltage levels (L and H) under the light load condition and non-light load condition heavier than light load. Accordingly, the decision means (28b) can correctly appreciate the load condition based on output signals of the current detector (9) at the transitional time of turning the switching element (3) from on to off, without any error in the decision resulted from capacitative short-circuit current such as surge current which may occur at the time of turning on of the switching element (3) so that the load condition on the secondary side of the transformer (2) can precisely and certainly be detected on the primary side of the transformer (2). Also, the decision on the load condition is hardly susceptible to influences of foreign noise such as inductive noise.

In a first embodiment of the present invention, the control circuit (8) is provided with an oscillation controller (22) which reduces the oscillation frequency of drive signals (V_G) when the decision means (28b) produces the output signal (V_{LD}) of the first voltage level (L), and adversely, increases the oscillation frequency of drive signals (V_G) when the decision means (28b) produces the output signal (V_{LD}) of the second voltage level (H). Under the light load condition, a small amount of electric current (I_D) flows through the primary winding (2a) of the transformer (2) or switching element (3) so that the decision means (28b) generates the output signal (V_{LD}) of the first voltage level (L) which reduces the oscillation frequency of drive signals (V_G) applied to the control terminal of the switching element (3) from the oscillation controller (22) to lower the switching number of the switching element (3). This allows decrease in switching loss during the light load period and also enhancement in conversion efficiency of the switching power source in a wider load fluctuation range.

In a second embodiment of the present invention, the control circuit (8) is provided with a voltage adjuster (31) which either controls the reference voltage level (V_{DT}) of the current comparator (27) in the same direction as the movement of peak voltage value of detection signal (V_{OCP}) by the current detector (9) or controls the voltage level of the detection signal (V_{OCP}) in the opposite direction from the movement of peak voltage value of detection signal (V_{OCP}) by the current detector (9), when the decision means (28b) changes the voltage level of the output signal (V_{LD}). Change in load causes the variation in oscillation frequency of drive signals (V_G) to change a maximum value of switching current (I_D) through the primary side. At the moment, the voltage adjuster (31) either controls the reference voltage level

(V_{DT}) of the current comparator (27) in the same direction as the movement of peak voltage value of detection signal (V_{OCP}) by the current detector (9) or controls the voltage level of the detection signal (V_{OCP}) in the opposite direction from the movement of peak voltage value of detection signal (V_{OCP}) by the current detector (9), to thereby stably alter oscillation frequency of the switching element (3) at the time of change in load.

In a third embodiment of the present invention, the control circuit (8) comprises a bottom voltage detector (41) for detecting a minimum level of the voltage (V_{DS}) between main terminals of the switching element (3) during the off period thereof; and a skip controller (42) which turns the switching element (3) on in response to a first minimum level (every minimum level) of the voltage (V_{DS}) detected by the bottom voltage detector (41) under the heavy load condition, that is, when the decision means (28b) produces the output signal (V_{LD}) of the second voltage level (H), otherwise, turns the switching element (3) on in response to a second or later minimum level (every other or later minimum level) detected by the bottom voltage detector (41) under the light load condition, that is, when the decision means (28b) produces the output signal (V_{LD}) of the first voltage level (L). In this way, under the light load condition, the switching element (3) is turned on in response to a second or later minimum level detected by the bottom voltage detector (41) to thereby expand the off period of the switching element (3), reducing the switching frequency of the switching element (3). Accordingly, decrease in switching number of the switching element (3) causes diminution in switching loss under the light load condition to improve conversion efficiency of the switching power source in a wider load fluctuation range. In another aspect, flyback energy in the transformer (2) is supplied from the second winding (2b) through the rectifying smoother (6) to load within a

relatively short period of time under the light load condition after the switching element (3) is turned off so that a narrow pulse voltage involving free oscillation components is produced across the switching element (3). Consequently, when the bottom voltage detector (41) detects a second or later minimum level of the narrow pulse voltage, the switching element (3) is turned on by the skip controller (42) to expand the off period of the switching element (3), lowering the switching frequency of the switching element (3). Under the heavier load condition than light load, flyback energy in the transformer (2) is supplied from the secondary winding (2b) through the rectifying smoother (6) to load over a relatively long period of time after the switching element (3) is turned off so that a wide pulse voltage is produced across the switching element (3). Therefore, when the bottom voltage detector (41) detects a first minimum level of the wide pulse voltage, the switching element (3) is turned on by the skip controller (42) so that pseudo resonance action is done to switch the switching element (3) from the off to the on condition at the time of the minimum level (bottom point) of the voltage (V_{DS}) across the switching element (3) after a reset period of the transformer (2) is finished. In the third embodiment, the bottom voltage detector (41) comprises a wave forming means for transforming, into pulse arrays, ringing voltages (V_{BM}) produced on a drive winding (2c) of the transformer (2) during the off period of the switching element (3), and the bottom voltage detector (41) may find a rising edge of the pulse array voltage (V_{BD}) as a minimum level of the voltage (V_{DS}) across the switching element (3).

A fourth embodiment of the present invention comprises a plurality of current comparators (27, 62), a plurality of edge detectors (28a) and a plurality of decision means (28b, 63) wherein the current comparators (27,

62) compare a detection signal (V_{OCP}) by current detector (9) with levels of different reference voltages (V_{DT1} , V_{DT2}) to reduce oscillation frequency of drive signals (V_G) to different frequencies by output signals (V_{LD1} , V_{LD2}) of the first level of the voltage output from the decision means (28b, 63). Under the light load condition, oscillation frequency of drive signals (V_G) applied to the control terminal of the switching element (3) can be lowered to different frequencies in response to the load condition to accomplish fine control of the oscillation frequency and improve conversion efficiency of the switching power source.

In a fifth embodiment of the present invention, the control circuit (8) comprises an intermittent oscillation controller (71) for suspending the on-off operation of the switching element (3) for a given period of time sufficiently longer than an oscillation cycle of the drive signals (V_G) when the decision means (28b) produces the output signal (V_{LD}) of the first voltage level (L). Under the light load condition wherein smaller electric current (I_D) flows through the primary winding (2a) of the transformer (2) or switching element (3), the output signal (V_{LD}) of the decision means (28b) is on the first voltage level (L) to cease the on-off operation of the switching element (3) by the intermittent oscillation controller (71) for a certain period of time (t_B) perfectly longer than the oscillation cycle of the drive signals (V_G), extremely reducing the switching number of the switching element (3). This allows steep reduction in the switching loss under the light load mode and attains enhancement in conversion efficiency of the switching power source in a wider load fluctuation range.

In each embodiment of the present invention, the edge detector (28a) and decision means (28b) may comprise a single D-flip flop (28). The

switching power source of the invention further comprises a trigger means (10) connected to the DC power source (1) for supplying the control circuit (8) with initial power during starting; a drive winding (2c) electromagnetically coupled to the primary and secondary windings (2a, 2b) of the transformer (2); and an auxiliary rectifying smoother (13) connected to the drive winding (2c) for providing the control circuit (8) with DC voltage (V_{IN}). It should be understood that the instant invention is applicable to a switching power source which includes a drive circuit for furnishing the control circuit (8) with drive power from the DC power source (1). In addition, the switching power source may comprise a switching element (91) provided with a divergent or shunt means (92) for dividing an electric current flow (I_D) through a closed circuit inclusive of the primary winding (2a) of the transformer (2) to detect by the current detector (9) the divided electric current through the divergent means (92).

BRIEF DESCRIPTION OF THE DRAWINGS

The above-mentioned and other objects and advantages of the present invention will be apparent from the following description in connection with preferred embodiment shown in the accompanying drawings wherein:

Figure 1 is a block circuit diagram indicating a basic concept of a switching power source according to the present invention;

Figure 2 shows a first embodiment of a DC-DC converter of separately excited flyback type which materializes the switching power source according to the present invention;

Figure 3 is a time chart indicating wave forms of input and output signals of D-flip flop with variation of switching current in the circuit shown

in Figure 2;

Figure 4 is a time chart indicating an electric current and voltages for various points in the circuit shown in Figure 2;

Figure 5 is an electric circuitry showing a second embodiment according to the present invention;

Figure 6 is an electric circuit diagram showing a voltage adjuster of Figure 5;

Figure 7 is an electric circuit diagram showing another embodiment of the voltage adjuster;

Figure 8 is a time chart indicating an electric current and voltages for various points in the circuit shown in Figure 5;

Figure 9 is an electric circuit diagram of a control circuit according to a third embodiment of the present invention;

Figure 10 is an electric circuit diagram of a bottom detector shown in Figure 9;

Figure 11 is a waveform diagram showing electric signals for various points in the bottom detector shown in Figure 10 with a voltage between drain and source terminals of a MOS-FET under the light load condition;

Figure 12 is an electric circuit diagram showing another embodiment of the bottom detector in Figure 9;

Figure 13 is a waveform diagram showing electric signals for various points with a voltage between drain and source terminals of the MOS-FET under the light load condition;

Figure 14 is a time chart indicating an electric current and voltages for various points in the circuit shown in Figure 9;

Figure 15 is a graph showing hysteretic characteristics under oscillation with load proportion;

Figure 16 is an electric circuit diagram showing a fourth embodiment

according to the present invention;

Figure 17 is a time chart showing an electric current and voltages for various points in the circuit of Figure 16;

Figure 18 is an electric circuit diagram of a fifth embodiment according to the present invention;

Figure 19 is a time chart showing an electric current and voltages for various points in the circuit of Figure 18;

Figure 20 is an electric circuit diagram of an embodiment to detect as a positive voltage a switching current in the circuit of Figure 2;

Figure 21 is a time chart showing an electric current and voltages for various points in the circuit of Figure 20;

Figure 22 is an electric circuit diagram of an embodiment according to the present invention to detect a DC output voltage on the secondary side through a drive winding;

Figure 23 is an electric circuit diagram of an embodiment using a current-sensible MOS-FET;

Figure 24 is an electric circuit diagram of Figure 16 incorporated with a skip controller;

Figure 25 is a time chart showing an electric current and voltages for various points in the circuit of Figure 24;

Figure 26 is an electric circuitry showing a prior art switching power source; and

Figure 27 is a waveform diagram of switching current under the heavy and light load conditions of the prior art switching power source.

BEST MODE FOR CARRYING OUT THE INVENTION

Embodiments of the switching power source according to the present

invention will be described hereinafter in connection with Figures 1 to 25 of the drawings.

Figure 1 is a block circuit diagram indicating a basic concept of a switching power source according to each embodiment of the present invention. The switching power source shown in Figure 1 comprises a DC power source 1; a primary winding 2a of a transformer 2 and a switching element or MOS-FET (Field Effect Transistor of MOS type) 3 connected in series to DC power source 1; a rectifying smoother 6 which comprises a rectifying diode 4 connected to a secondary winding 2b of transformer 2 and a smoothing capacitor 5 to generate DC output voltage V_{OUT} ; a voltage detector (output voltage detecting circuit) 7 for sensing DC output voltage V_{OUT} ; a control circuit 8 which comprise a driver 25 for receiving detection signals V_{FB} from voltage detector 7 and supplying MOS-FET 3 with drive signals V_G to turn MOS-FET 3 on and off so as to keep DC output voltage V_{OUT} on a substantially constant level; and a current detector (current-detecting resistor) 9 for acquiring electric current I_D flowing through primary winding 2a of transformer 2 or MOS-FET 3. Control circuit 8 comprises a current comparator (current-detecting comparator) 27 for comparing a voltage level V_{OCP} of signals acquired by current detector 9 with a reference voltage level V_{DT} to produce detection signals V_{CP} of first and second level L and H when acquired voltage level V_{OCP} respectively does not reach and exceed reference voltage level V_{DT} ; an edge detector 28a for sensing an edge of drive signal V_G supplied to a control or gate terminal of MOS-FET 3 during the transition period from turning on to off of MOS-FET 3; and a decision means 28b for receiving a current detection signal V_{CP} from current comparator 27 to produce an output signal V_{LD} when edge detector 28a catches an edge of drive signal V_G . In the power source shown in Figure

1, decision means 28b produces different output signals V_{LD} of respectively first and second voltage levels L and H under the light and ordinary load conditions. This ordinary load is shown by the second voltage level H as meaning a load heavier than light load, and ranging from an intermediate or normal load to heavy load. In embodiments shown in and after Figure 2, edge detector 28a and decision means 28b may comprise a single D-flip flop 28.

Figure 2 demonstrates an embodiment of DC-DC converter of separately excited flyback type as a switching power source according to the present invention. This DC-DC converter of Figure 2 comprises a DC power source 1 which includes a rectifying bridge circuit 1c connected to an AC power source 1a through a filter circuit 1b and a smoothing capacitor 1d connected to rectifying bridge circuit 1c; a primary winding 2a of a transformer 2 and a MOS-FET 3 connected in series to DC power source 1; a rectifying smoother 6 which comprises a rectifying diode 4 connected to a secondary winding 2b of transformer 2 and a smoothing capacitor 5 to generate DC output voltage V_{OUT} ; a voltage detector (output voltage detecting circuit) 7 for sensing DC output voltage V_{OUT} ; a control circuit 8 which receives detection signals V_{FB} from voltage detector 7 and supplying MOS-FET 3 with drive signals V_G to turn MOS-FET 3 on and off so as to keep DC output voltage V_{OUT} on a substantially constant level; and a current detector or detection resistor 9 for acquiring as a negative voltage electric current I_D flowing through primary winding 2a of transformer 2 or MOS-FET 3; a trigger resistor 10 as a trigger means connected to rectifying bridge circuit 1c of DC power source 1 for supplying control circuit 8 with initial drive power during starting; a drive winding 2c electromagnetically coupled to primary and secondary windings 2a, 2b of transformer 2; and an auxiliary rectifying smoother 13 connected to drive winding 2c for providing control

circuit 8 with DC voltage V_{IN} . Detection outputs from voltage detector 7 is forwarded to primary side of transformer 2 through a photo-coupler 14 of light emitting and receiving elements 14a and 14b to deliver an induced voltage V_{FB} on a junction of light receiving element 14b and resistor 15 to control circuit 8 as induced voltage V_{FB} indicates a detection output from voltage detector 7.

Control circuit 8 comprises a controlled power source 16 for producing a reference voltage V_{RC} as a reference voltage generator to regulate a maximum value of current flow through primary winding 2a of transformer 2 or MOS-FET 3; adjustment resistors 17 and 18 for shifting a negative voltage level acquired by detection resistor 9; a restrictive comparator 19 for outputting an electric signal V_1 of high voltage level H to turn MOS-FET 3 off when level-shifted detection signal V_{OCP} by detection resistor 9 reaches reference voltage V_{RC} of power source 16; a regulatory comparator 20 for outputting an electric signal V_2 of high voltage H when level-shifted detection signal V_{OCP} of detection resistor 9 reaches voltage level of detection signal V_{FB} from voltage detector 7; an OR gate 21 for outputting logical sum signal V_3 of outputs V_1 and V_2 from restrictive and regulatory comparators 19 and 20; a pulse generator 22 for outputting pulse signal V_4 each time a constant time has elapsed after MOS-FET 3 is turned off; an RS flip flop 23 set by pulse signal V_4 from pulse generator 22 to provide gate terminal of MOS-FET 3 with drive signal V_G of high voltage level H, and reset by logical sum signal V_3 from OR gate 21 to provide gate terminal of MOS-FET 3 with drive signal V_G of low voltage level L; a control power circuit 24 for supplying each element 16 to 28 of control circuit 8 with DC drive power when DC voltage V_{IN} from trigger resistor 10 or auxiliary rectifying smoother 13 reaches a given DC voltage V_{IN} , and also for ceasing supply of DC drive

power to each elements 16 to 28 when DC voltage V_{IN} is reduced to an inoperable level; a power source 26 for producing a reference voltage V_{DT} which regulates a voltage level to examine a load condition not shown; a current detection comparator 27 as a current detection cooperating means for outputting current detection signals of low and high voltage levels L and H respectively when shifted or divided voltage level V_{OCP} from detection resistor 9 does not reach and exceed reference voltage level V_{DT} of power source 26; and a D-flip flop 28 having a clock input terminal CLK for receiving drive signals V_G also applied to gate terminal of MOS-FET 3. D-flip flop 28 firstly takes in, through data input terminal D, current detection signal V_{CP} produced from current detection comparator 27 when drop or trailing edge of drive signals V_G applied to gate terminal of MOS-FET 3 upon the transition of turning MOS-FET 3 from the on to the off condition, secondly generates from output terminal Q output signals V_{LD} of the substantially same voltage level as that of current detection signals V_{CP} , and thirdly retains output signals V_{LD} until a subsequent trailing edge of drive signal V_G has again inputted to clock input terminal CLK after the previous trailing edge of drive signals V_G is inputted. Driver 25 shown in Figure 1 comprises a regulatory comparator 20, OR gate 21, pulse generator 22 and RS flip flop 23. Pulse generator 22 comprises an oscillation controller which elongates occurrence cycle of pulse signals V_4 when D-flip flop 28 produces output signals V_{LD} of low voltage level L to lower oscillation frequency of drive signals V_G by extending off-time of drive signals V_G applied from RS flip flop 23 to gate terminal of MOS-FET 3. Adversely, oscillation controller of pulse generator 22 shortens occurrence cycle of pulse signals V_4 when D-flip flop 28 produces output signals V_{LD} of high voltage level H to increase oscillation frequency of drive signals V_G by reducing off-time of drive signals V_G applied from RS flip flop 23 to gate terminal of MOS-FET 3. Off-time of

drive signals V_G , namely time for keeping drive signals V_G in low voltage level is set in a range for example between 10 to 50 microseconds. Also, voltage level on current detection resistor 9, in other words, junction voltage V_{OCP} of level-shifting resistors 17 and 18 is set by appropriate adjustment of each resistance value of resistors 17 and 18, for example, as zero volt before starting, and as 1.5 volts after starting and when electric current I_D through MOS-FET 3 is zero.

Figure 3(A) to 3(E) represents each waveform of drive signals V_G applied to gate terminal of MOS-FET 3, drain current I_D through MOS-FET 3, voltage V_{OCP} on a junction of level-shifting resistors 17 and 18, current detection signal V_{CP} from current detection comparator 27 and output signals V_{LD} from D-flip flop 28. Figure 3(A) shows drive signals V_G applied to gate terminal of MOS-FET 3 wherein voltage level of drive signal V_G is elevated from low voltage L to high voltage H at point t_0 under the heavy and normal load conditions. Therefore, MOS-FET 3 is turned on so that capacitative short-circuit current instantaneously flows through MOS-FET 3, and drain current I_D rapidly increases as shown in Figure 3(B). As a result, as divided voltage V_{OCP} is lowered below reference voltage level V_{DT} of power source 26 as shown in Figure 3(C), current detection comparator 27 produces current detection signal V_{CP} of high voltage level H as shown in Figure 3(D). Then, when divided voltage V_{OCP} reaches above reference voltage level V_{DT} of power source 26 at point t_1 , voltage level of current detection signal V_{CP} is turned from high voltage level H to low voltage level L.

When MOS-FET 3 is turned on, drain current I_D linearly increases as depicted in Figure 3(B), and simultaneously divided voltage V_{OCP} linearly decreases. Then, when divided voltage V_{OCP} reduces beneath reference

voltage level V_{DT} of power source 26 at point t_2 , current detection signal V_{CP} from current detection comparator 27 is switched from low voltage level L to high voltage level H as shown in Figure 3(D). At the time drive signals V_G applied to gate terminal of MOS-FET 3 is turned from high voltage level H to low voltage level L at point t_3 , MOS-FET 3 is turned from on to off condition. At this point, as current detection signal V_{CP} from current detection comparator 27 remains on high voltage level H as shown in Figure 3(D), under the light load condition before point t_0 , D-flip flop 28 changes signal V_{LD} from output terminal Q from low voltage level L to high voltage level H as shown in a solid line of Figure 3(E). Otherwise, under the heavy and normal load conditions before point t_0 , signal V_{LD} outputted from output terminal Q of D-flip flop 28 is retained on high voltage level H as shown by dotted line of Figure 3(E). Accordingly, under the heavy and normal load conditions, D-flip flop 28 produces output signal V_{LD} of high voltage level H from output terminal Q to generate pulse signals V_4 of shorter cycle from pulse generator 22.

When MOS-FET 3 is turned off, drain current I_D gradually decreases as shown in Figure 3(B) due to response delay of MOS-FET 3 itself or Miller effect resulted from stray capacitance of MOS-FET 3 etc., and simultaneously, divided voltage V_{OCP} gradually increases as shown in Figure 3(C). In case voltage V_{OCP} increases over reference voltage V_{DT} of power source 26 at point t_4 , current detection signal V_{CP} from current detection comparator 27 is switched from high voltage level H to low voltage level L as shown in Figure 3(D), and drain current I_D comes to substantially zero at a point t_5 as shown in Figure 3(B).

When the situation is moved from the heavy and normal load

conditions to the light load condition, drive signal V_G applied to gate terminal of MOS-FET 3 is shifted from low voltage level L to high voltage level H at point t_6 as shown in Figure 3(A) to turn MOS-FET 3 on so that capacitive short-circuit current instantaneously flows through MOS-FET 3 similarly to the above-mentioned operation during the period of time between points t_0 and t_1 , rapidly increasing drain current I_D as exhibited in Figure 3(B). At the same time, as divided voltage V_{OCP} is diminished under reference voltage V_{DT} of power source 26 as indicated by Figure 3(C), current detection comparator 27 produces current detection signal V_{CP} of high voltage level H as shown in Figure 3(D). After that, when voltage V_{OCP} increases over reference voltage V_{DT} of power source 26 at point t_7 , comparator 27 changes current detection signal V_{CP} from high voltage level H to low voltage level L. When MOS-FET 3 is turned on, drain current I_D linearly increases as shown in Figure 3(B), however, to the contrary, divided voltage V_{OCP} linearly decreases as shown in Figure 3(C). As on-time of MOS-FET 3 under the light load condition is shorter than on-time between points t_0 and t_3 under the heavy and normal load conditions, drive signal V_G is switched from high voltage level H to low voltage level L at relatively early point t_8 as shown in Figure 3(A) to turn MOS-FET 3 from on to off condition. For that reason, divided voltage V_{OCP} does not reach reference voltage V_{DT} of power source 26 as shown in Figure 3(C), and current detection signal V_{CP} from current detection comparator 27 is retained on low voltage level L as shown in Figure 3(D). As a result, D-flip flop 28 switches output signal V_{LD} at output terminal Q from high voltage level H to low voltage level L at point t_8 under the light load condition to generate pulse signals V_4 of longer cycle from pulse generator 22.

In initially operating DC-DC converter of separately excited flyback

type shown in Figure 2, charging current flows from DC power source 1 through trigger resistor 10 to a smoothing drive capacitor 12 of auxiliary rectifying smoother 13. When charged voltage V_{IN} of drive capacitor 12 reaches a drive voltage, control power source 24 in control circuit 8 starts supplying DC power to each element 16 to 28 in control circuit 8. Accordingly, pulse generator 22 is driven to give a set terminal S of RS flip flop 23 a pulse signal V_4 from pulse generator 22 so that RS flip flop 23 is turned to the set condition to supply gate terminal of MOS-FET 3 with drive signals V_G of high voltage level H from RS flip flop and thereby turn MOS-FET 3 on. At this moment, linearly increasing drain current I_D flows through MOS-FET 3, whereas divided voltage V_{OCP} linearly decreases. When voltage V_{OCP} is lowered to reference voltage V_{RC} of power source 16, overcurrent control comparator 19 produces signal V_1 of high voltage level H. Meanwhile, as voltage detector 7 produces detection signal V_{FB} of substantially zero voltage level during starting, current mode controlling comparator 20 produces output signal V_2 of low voltage level L. Accordingly, OR gate 21 outputs a logic sum signal V_3 of high voltage level H to input terminal R of RS flip flop 23 to reset RS flip flop 23 which provides gate terminal of MOS-FET 3 with drive signal V_G of low voltage level L to turn MOS-FET 3 off so that drain current I_D through MOS-FET 3 declines to nearly zero level. When a period of time has lapsed after MOS-FET 3 is turned off, pulse generator 22 again gives set terminal S of RS flip flop 23 pulse signal V_4 to switch RS flip flop 23 to the set condition so that RS flip flop 23 supplies gate terminal of MOS-FET 3 with drive signal of high voltage level H to again turn MOS-FET 3 on. In this way, repeated on-and-off operation causes linear rise in DC output voltage V_{OUT} from rectifying smoother 6, while charged voltage V_{IN} on drive capacitor 12 linearly falls. However, as drive winding 2c generates drive voltage proportional to voltage induced on secondary winding 2b of

transformer 2, auxiliary rectifying smoother 13 produces directly rising DC voltage V_{IN} with elevation of DC output voltage V_{OUT} . Therefore, DC voltage V_{IN} applied to control power source circuit 24 in control circuit 8 drops nearly to a disabling level, and then again linearly rises. Accordingly, control power source circuit 24 in control circuit 8 is operated by DC voltage V_{IN} from auxiliary rectifying smoother 13 after starting. Detection signal voltage V_{FB} from voltage detector 7 also linearly rises from zero volt with elevation of DC output voltage V_{OUT} from rectifying smoother 6 on the secondary side.

When voltage level of detection signal V_{FB} from output voltage detector 7 becomes higher than reference voltage V_{RC} of power source 16, and divided voltage V_{OCP} reaches voltage level of detection signal V_{FB} from output voltage detector 7, mode control comparator 20 produces signal V_2 of high voltage level H. While over-current restricting comparator 19 produces signal V_1 of low voltage level L, OR gate 21 produces logic sum signal V_3 of high voltage level H to reset input terminal R of RS flip flop 23 to switch RS flip flop 23 to the reset condition. Accordingly, RS flip flop 23 forwards drive signal V_G of low voltage level L to gate terminal of MOS-FET 3 to turn MOS-FET 3 off, thereby causing drain current I_D through MOS-FET 3 to fall to nearly zero. At this time, output current I_{OUT} from secondary winding 2b of transformer 2 flows to load not shown through rectifying smoother 6, and then linearly increases. Subsequently, when DC output voltage V_{OUT} from rectifying smoother 6 reaches a detection voltage determined by various constants of each element which forms voltage detector 7, the operation moves from starting condition to normally operating condition to make all of DC voltage V_{IN} from auxiliary rectifying smoother 13, DC output voltage V_{OUT} and output current I_{OUT} from rectifying smoother 6 substantially constant. The above detection signal is expressed by a formula: $\{(R_1 + R_2)/$

$R_2 \times (V_Z + V_{BE}) / V$) wherein a fraction: $R_2 / (R_1 + R_2)$ denotes a divided ratio of dividing resistors between output terminals; V_Z denotes a Zener voltage of a Zener diode; V_{BE} denotes a voltage between base and emitter terminals of a NPN transistor on the order of 0.6 to 0.7 volt.

Under the normal load condition, RS flip flop 23 produces drive signals of high voltage level H shown in Figure 4(B) to gate terminal of MOS-FET 3 to turn MOS-FET 3 on so that linearly increasing drain current I_D flows through MOS-FET 3, and simultaneously divided voltage V_{OCP} linearly decreases as shown in Figure 4(D). Here, as voltage level of detection signal V_{FB} from output voltage detector 7 is lower than reference voltage level V_{DT} of power source 26 under the normal load condition as shown in Figure 4(D), divided voltage V_{OCP} falls beneath reference voltage level V_{DT} of power source 26 to voltage level of detection signal V_{FB} from output voltage detector 7, and accordingly, current detection comparator 27 produces current detection signal V_{CP} of high voltage level H. Further, when divided voltage V_{OCP} reaches voltage level of detection signal V_{FB} from output voltage detector 7, current mode controlling comparator 20 produces signal V_2 of high voltage level H. At this moment, while over-current control comparator 19 produces signal V_1 of low voltage current L, OR gate 21 forwards logical sum signal V_3 of high voltage level H to reset terminal of RS flip flop 23 to reset it. Therefore, RS flip flop 23 provides gate terminal of MOS-FET 3 with drive signal V_G switched from high voltage level H to low voltage level L to turn MOS-FET 3 from on to off, causing drain current I_D through MOS-FET 3 to drop to substantially zero as shown in Figure 4(A). At this time, trailing edge (shown by arrows in Figure 4(B)) of drive signal V_G is given to clock input terminal CLK of D-flip flop 28, and simultaneously, current detection comparator 27 furnishes signal input terminal D of D-flip flop 28 with

current detection signal V_{CP} of high voltage level H to keep signal V_{LD} from output terminal Q on high voltage level H as shown in Figure 4(C). Accordingly, pulse generator 22 produces pulse signals V_4 of shorter cycle to reduce off-period of MOS-FET 3 and increase oscillation frequency.

When load not shown becomes light, DC output voltage V_{OUT} from rectifying smoother 6 on the secondary side increases, and voltage of detection signal V_{FB} from output voltage detector 7 linearly rises above reference voltage level V_{DT} of power source 26. If RS flip flop 23 provides gate terminal of MOS-FET 3 with drive signal V_G of high voltage level H shown in Figure 4(B) to turn MOS-FET 3 on, drain current I_D passes through MOS-FET 3 and directly increases, and at the same time, divided voltage V_{OCP} linearly drops to voltage level of detection signal V_{FB} from output voltage detector 7. Here, as voltage level of detection signal V_{FB} from output voltage detector 7 under the light load condition is higher than reference voltage V_{DT} of power source 26, divided voltage V_{OCP} does not reach reference voltage V_{DT} of power source 26 to generate current detection signal V_{CP} of low voltage level from current detection comparator 27. When divided voltage V_{OCP} reaches voltage level of detection signal V_{FB} from output voltage detector 7 as understood from Figure 4(D), current mode controlling comparator 20 produces an output signal V_2 of high voltage level H. In another aspect, since over-current control comparator 19 sends a signal V_1 of low voltage level L to OR gate 21 which then outputs logical sum signal V_3 of high voltage level to reset terminal R of RS flip flop 23 to reset it. Accordingly, as shown in Figure 4(B), RS flip flop 23 switches drive signal V_G from high voltage level H to low voltage level L to gate terminal of MOS-FET 3 to turn MOS-FET 3 from on to off, thereby causing drain current I_D through MOS-FET 3 to drop to nearly zero. At this moment, as D-flip flop 28

receives drop or trailing edge (shown by an arrow) of drive signal V_G shown in Figure 4(B) at clock input terminal CLK and simultaneously current detection signal V_{CP} of low voltage level L from current detection comparator 27 at signal input terminal D, it switches signal V_{LD} from output terminal Q from high voltage level H to low voltage level L to elongate cycle of pulse signal V_4 from pulse generator 22 for off-period extension of MOS-FET 3 and reduction of oscillation frequency.

In this embodiment, at the transitional time from turning-on to -off of MOS-FET 3, D-flip flop 28 can produce its signals V_{LD} of correct voltage level to precisely and certainly appreciate on the primary side of transformer 2 the load condition on the secondary side of transformer 2 based on output signals of current detector 9 without any erroneous appreciation resulted from capacitative short-circuit current such as surge current which may occur at the time of turning on of MOS-FET 3. Also, the power source is advantageous in that the appreciation on the load condition is almost immune to foreign noise such as inductive noise. In addition, under the light load condition wherein a small amount of drain current I_D flows through primary winding 2a of transformer 2 or MOS-FET 3, D-flip flop 28 produces output signals V_{LD} of low voltage level L to extend occurrence cycle of pulse signals V_4 of pulse generator 22. This allows off-period of MOS-FET 3 to extend and oscillation frequency of drive signals V_G to gate terminal of MOS-FET 3 to decrease, thereby causing switching number of MOS-FET 3 to lessen switching loss under the light load condition and improve conversion efficiency of the switching power source in a wide load fluctuation range.

The foregoing embodiments can be varied. For example, Figure 5 illustrates a varied embodiment of the DC-DC converter of separately excited

flyback type which comprises a voltage level adjuster 31 provided in control circuit 8 as a voltage level adjusting means for changing reference voltage level V_{DT} of power source 26 in the same direction as that for movement of a peak value of divided voltage V_{OCP} when D-flip flop 28 switches voltage level of output signal V_{LD} . As shown in Figure 6, voltage level adjuster 31 comprises a first dividing resistor 32 whose one end is connected to a positive electrode of reference power source 16; a second dividing resistor 33 and NPN transistor 34 connected in series between the other end of first dividing resistor 32 and a negative electrode of reference power source 16; and an inverter 35 connected between an output terminal Q of D-flip flop 28 and a base terminal of NPN transistor 34. When under the heavy or normal load condition, D-flip flop 28 produces output signal V_{LD} of high voltage level H as shown in Figure 8(C), a junction of dividing resistors 32 and 33 produces reference voltage V_{DTH} of high voltage level shown in Figure 8(D) with NPN transistor 34 in the off condition. Then, when D-flip flop 28 has changed output signal V_{LD} from high voltage level H to low voltage level L, NPN transistor 34 is turned on to produce a low level reference voltage V_{DTL} shown in Figure 8(D) from junction of dividing resistors 32 and 33. When load has become light, and D-flip flop 28 has changed output signal V_{LD} from high voltage level H to low voltage level L as shown in Figure 8(C), low level period of drive signals V_G is extended as shown in Figure 8(B) to reduce oscillation frequency, and as a result, drain current I_D flows through MOS-FET 3 with the slightly rising peak value. In association with this, negative peak values of divided voltage V_{OCP} slightly moves downward. At the moment, NPN transistor 34 of voltage level adjuster 31 is turned on, and junction voltage of first and second dividing resistors 32 and 33 is switched from high voltage level V_{DTH} to low voltage level V_{DTL} as shown in Figure 8(D) to stabilize voltage level of output signals V_{LD} from D-flip flop 28 after the

switching and stably shift oscillation mode of MOS-FET 3 at the time of load transition.

Figure 7 shows another embodiment of voltage level adjuster 31 for changing voltage V_{OC} in the adverse direction from that of peak level movement of divided voltage V_{OC} when D-flip flop 28 switches voltage level of output signals V_{LD} . Voltage level adjuster 31 comprises a PNP transistor 36 and a resistor 37 connected in series between both ends of level-shifting resistor 7 to raise divided voltage V_{OC} when D-flip flop 28 supplies base terminal of PNP transistor 36 with output signal V_{LD} of low voltage level. Specifically, if the situation has changed to the light load condition such that D-flip flop 28 switches output signal V_{LD} from high voltage level H to low voltage level L, PNP transistor 36 is turned on to feed electric current through level-shifting resistor 17 and resistor 37 in parallel, thereby increasing divided voltage V_{OC} . Accordingly, similarly to the embodiment shown in Figure 6, voltage level adjuster 31 also shown in Figure 7 enables D-flip flop 28 to stabilize voltage level of output signals V_{LD} and stably shift oscillation mode of MOS-FET 3 at the time of load change.

Figure 9 illustrates a control circuit 8 similar to that provided in DC-DC converter of separately excited flyback type shown in Figure 5 except that control circuit 8 of Figure 9 comprises a bottom detecting circuit 41 as a bottom detection means for detecting minimum levels of voltage V_{DS} between drain and source terminals of MOS-FET 3 during the off-period of MOS-FET 3; and a skip control circuit 42 as a skip control means for turning MOS-FET 3 on at the time bottom detecting circuit 41 finds a first minimum level of voltage V_{DS} when D-flip flop 28 produces output voltage V_{LD} of high voltage level H, and also for turning MOS-FET 3 off at the time bottom detecting

circuit 41 finds a second minimum level of voltage V_{DS} when D-flip flop 28 produces output voltage V_{LD} of low voltage level. As illustrated in Figure 10, bottom detecting circuit 41 comprises a diode 43 and voltage dividing resistors 44 and 45 connected in series between both ends of drive winding 2c of transformer 2; a capacitor 46 connected in parallel to resistor 45; a reference power source 47 for providing a threshold voltage V_{TH} ; and a comparator 48 for generating output V_{BD} of low voltage level L and high voltage level H respectively when charged voltage V_{BM} of capacitor 46 is lower than and higher than threshold voltage V_{TH} of reference power source 47. In other words, bottom detecting circuit 41 of Figure 10 provides a waveform shaping means for transforming, into shapes shown in Figure 11(C) through diode 43, resistors 44 and 45 and capacitor 46, ringing voltages similar in shape to voltages V_{DS} (Figure 11(A)) between drain and source terminals of MOS-FET 3 which appear on drive winding 2c of transformer 2 during the off-period of MOS-FET 3; and moreover transforming the waveform of Figure 11(C) into pulse array voltages V_{BD} shown in Figure 11(D) by comparing charged voltage V_{BM} in capacitor 46 shown in Figure 11(C) with threshold voltage V_{TH} of reference power source 47 by means of comparator 48. In this way, minimum level of voltage V_{DS} between drain and source terminals of MOS-FET 3 can be detected in the form of trailing or drop edges of pulse array voltage V_{BD} produced from comparator 48.

On the other hand, bottom detecting circuit 41 may be designed as shown in Figure 12 to include voltage dividing resistors 44 and 45 connected to both ends of drive winding 2c of transformer 2; a reference power source 47 for providing a threshold voltage V_{TH} ; a comparator 48 for producing output V_{BD} of low voltage level L and high voltage level H respectively when

divided voltage V_{BM} on junction of resistors 44 and 45 is lower and higher than level of threshold voltage V_{TH} of reference power source 47; and a retardant circuit 49 for delaying pulse array voltage V_{BD} from comparator 48 by a period of time t_D . Specifically, in bottom detecting circuit 41 shown in Figure 12, voltage dividing resistors 44 and 45 divides ringing voltages similar in shape to voltages V_{DS} (Figure 13(A)) between drain and source terminals of MOS-FET 3 which appear on drive winding 2c of transformer 2 during the off-period of MOS-FET 3; comparator 48 compares voltage V_{BM} with threshold voltage V_{TH} of power source 47 to transform voltages V_{DS} of Figure 13A into pulse array voltages V_{BD} shown in Figure 13(D); and retardant circuit 49 delays pulse array voltages V_{BD} from comparator 48 by a period of time t_D to synchronize trailing edge of pulse array voltage V_{BD} from comparator 48 with minimum level of voltage V_{DS} between drain and source terminals of MOS-FET 3 as shown in Figure 13(A) to 13(D). In this way, bottom detecting circuit 41 enables detection of a minimum point on voltage V_{DS} between drain and source terminals of MOS-FET 3 in the form of trailing edge of pulse array voltage V_{BD} from comparator 48.

As shown in Figure 9, skip control circuit 42 involves first and second D-flip flops 50 and 51 each which has a reset terminal R for resetting them by rising edge of drive signals for MOS-FET 3. Output signals V_{BD} from bottom detecting circuit 41 are given to each clock input terminal CLK of first and second D-flip flops 50 and 51; an input terminal D of first D-flip flop 50 is retained on high voltage level (REG); an input terminal D of second D-flip flop 51 is connected to output terminal Q of first D-flip flop 50; and input terminals of OR gate 53 are connected to output terminal Q of second D-flip flop 51, output terminals of pulse generator 22 and AND gate 52. One input terminal of AND gate 52 is connected to output terminal Q of first D-

flip flop 50, and the other input terminal of AND gate 52 is connected to output terminal Q of D-flip flop 28. An output terminal of OR gate 53 is connected to a set terminal S of RS flip flop 23. First D-flip flop 50 produces output signal V_{DF1} of high voltage level H synchronously with trailing edge of a first output signal V_{BD} from bottom detecting circuit 41 to clock input terminals CLK. Second D-flip flop 51 produces output signal V_{DF2} of high voltage level H synchronously with trailing edge of a second output signal V_{BD} from bottom detecting circuit 41 to clock input terminals CLK. In skip control circuit 42 shown in Figure 9, under the heavy and normal load conditions, D-flip flop 28 produces output signal V_{LD} of high voltage level H, and first D-flip flop 50 produces output signal V_{DF1} of high voltage level H synchronously with trailing edge of a first output signal V_{BD} from bottom detecting circuit 41 to clock input terminal CLK of first D-flip flop 50 to produce output signal V_{AD} of high voltage level H from AND gate 52. Output signal V_{AD} from AND gate 52 is supplied through OR gate 53 to set terminal S of RS flip flop 23 to provide gate terminal of MOS-FET 3 with drive signal V_G of high voltage level H. Accordingly, under the heavy and normal load conditions, MOS-FET 3 can be turned on at the first minimum point on voltage detected by bottom detecting circuit 41. To the contrary, since D-flip flop 28 produces output signal V_{LD} of low voltage level L under the light load condition, AND gate 52 produces output signal V_{AD} of low voltage level L which can never turn RS flip flop 23 to the set condition. Meanwhile, since second D-flip flop 51 changes output signal V_{DF2} to high voltage level H synchronously with trailing edge of a second output signal V_{BD} from bottom detecting circuit 41 to clock input terminal CLK of second D-flip flop 51, output signal V_{DF2} is supplied through OR gate 53 to set terminal S of RS flip flop 23 to provide gate terminal of MOS-FET 3 with drive signal V_G of high voltage level H. For that reason, MOS-FET 3 can be turned on at the second

minimum point on voltage detected by bottom detecting circuit 41 under the light load condition.

In operation of DC-DC converter of separately excited flyback type shown in Figure 9, during the heavy and normal load period, D-flip flop 28 produces output signal V_{LD} of high voltage level H as shown in Figure 14(D), and simultaneously, first D-flip flop 50 of skip control circuit 42 produces a single pulsatile signal V_{DF1} from output terminal Q synchronously with a first trailing edge of output signal V_{BD} from bottom detecting circuit 41 as shown in Figure 14(C). Accordingly, in synchronization with the first trailing edge of output signal V_{BD} from bottom detection circuit 41, AND gate 52 produces a single pulsatile logical sum signal V_{AD} of high voltage level. Also, as second D-flip flop 51 of skip control circuit 42 produces signal V_{DF2} of low voltage level L at output terminal Q, OR gate 53 sends a single pulsatile logical sum signal V_{OR} of high voltage level H to RS flip flop 23, synchronously with a first trailing edge of output signal V_{BD} from bottom detecting circuit 41 to switch RS flip flop 23 to the set condition. As a result, as shown in Figure 14(C) and 14(B), RS flip flop 23 changes drive signal V_G from low voltage level L to high voltage level H to gate terminal of MOS-FET 3 in synchronization with a first trailing edge of output V_{BD} from bottom detecting circuit 41 to turn MOS-FET 3 on. At the moment, as shown in Figure 14(A), linearly increasing drain current I_D flows through MOS-FET 3, and simultaneously divided voltage V_{OCP} linearly falls under reference voltage V_{DTH} of high level as shown in Figure 14(E). When divided voltage V_{OCP} reaches a voltage level of detection signal V_{FB} from voltage detecting circuit 7, current mode control comparator 20 produces a signal V_2 of high voltage level to reset RS flip flop 23. Thus, RS flip flop 23 switches drive signal V_G from high voltage level H to low voltage level L to gate terminal of

MOS-FET 3 as shown in Figure 14(B) to turn MOS-FET 3 off. In other words, under the heavy and normal load conditions and during the off-period of MOS-FET 3, flyback energy stored in transformer 2 is discharged to the end, and when voltage V_{DS} between drain and source terminals reaches every minimum voltage point (bottom point), MOS-FET 3 is turned on to perform pseudo resonance.

When load becomes light so that D-flip flop 28 switches output signal V_{LD} from high voltage level H to low voltage level L, drain current I_D through MOS-FET 3 slightly raises the maximum value as shown in Figure 14(A), and at the same time, divided voltage V_{OCP} slightly lowers the negative peak. Just then, voltage regulator 31 changes the reference voltage to non-inverted input terminal (+) of current detecting comparator 27 from high level V_{DTH} to low level V_{DTL} . Moreover, second D-flip flop 51 of skip control circuit 42 produces a single pulsatile signal V_{DF2} at output terminal Q synchronously with a second trailing edge of output signal V_{BD} shown in Figure 14(C) from bottom detection circuit 41. Also, although AND gate 52 produces signal V_{AD} of low voltage level L, OR gate 53 produces single pulsatile logical sum signal V_{OR} of high voltage level synchronously with single pulsatile signal V_{DF2} from D-flip flop 51 to set RS flip flop 23. Accordingly, RS flip flop 23 changes drive signal V_G from low voltage level L to high voltage level H to gate terminal of MOS-FET 3 synchronously with the second trailing edge of output signal V_{BD} from bottom detection circuit 41 as shown in Figure 14(B) and 14(C) to turn MOS-FET 3 on. Thus, linearly increasing drain current flows through MOS-FET 3 as shown in Figure 14(A), and simultaneously divided voltage V_{OCP} linearly decreases. At the moment, as detection signal V_{FB} from output voltage detector 7 is higher than reference voltage V_{DTL} of low voltage level, divided voltage V_{OCP} does not reach reference voltage level V_{DTL} . When

divided voltage V_{OCP} reaches detection signal V_{FB} from output voltage detector 7, current mode control comparator 20 produces output signal V_2 of high voltage level H to reset RS flip flop 23. Accordingly, as shown in Figure 14(B), RS flip flop 23 changes drive signal V_G from high voltage level H to low voltage level L to gate terminal of MOS-FET 3 to turn MOS-FET 3 from on to off condition. In this way, under the light load condition, MOS-FET 3 is turned on as “bottom skipping” at the second minimum voltage point or at every other minimum voltage point of voltage V_{DS} between drain and source terminals which occurs during the off-period of MOS-FET 3.

Figure 15 shows a transitional diagram of oscillation to load proportion in the DC-DC converter of separately excited flyback type. The term “load proportion” means a proportion of power consumed by load to power which the converter can output to load. 50 to 100% of load proportion means the normal and heavy load conditions involving the pseudo resonance, while 0 to 70% of load proportion means the normal and light load conditions involving the bottom skipping. When load becomes light with the load proportion falling from 100% to 50%, the converter changes from pseudo resonance to bottom skipping, and it keeps bottom skipping until unloaded condition or zero % such as standby condition for load. When load becomes heavier than the unloaded condition with the increasing load proportion from zero % to 70%, operation moves from bottom skipping to pseudo resonance which is kept under the heavy load condition or up to 100% load proportion. In this way, pseudo resonance and bottom skipping cooperate together to provide the operation in DC-DC converter with the hysteretic characteristics in the transitional graph of load proportion shown in Figure 15. Substitution of the switching frequency reducing operation for the bottom skipping shown in Figure 15, would be able to draw a transitional graph of oscillation for DC-

DC converter shown in Figure 5.

In the embodiment of Figure 9, MOS-FET 3 is turned on at the second minimum voltage point of voltage V_{DS} between drain and source terminals of MOS-FET 3 under the light load condition to extend the off-period of MOS-FET 3 for reduction in switching frequency or switching number of MOS-FET 3, resulting in decrease in switching loss and improvement in conversion efficiency in a wide operation range of switching power source. In other words, as flyback energy in transformer 2 causes output current to flow from secondary winding 2b through rectifying smoother 6 to load not shown for a short period of time after MOS-FET 3 is turned off, voltage pulses V_{DS} of narrow time width occur between drain and source terminals of MOS-FET 3 as shown in Figures 11(A) and 13(A) accompanying free oscillation components. Accordingly, MOS-FET 3 is turned on when bottom detecting circuit 41 finds a second minimum voltage point of narrow voltage pulses V_{DS} under the light load condition to carry out the bottom skipping by skip control circuit 42, extending the off-period of MOS-FET 3 and reducing oscillation frequency. Also, under the heavy and normal load conditions, flyback energy in transformer 2 causes output current to flow from secondary winding 2b through rectifying smoother 6 to load for a long period of time after MOS-FET 3 is turned off, thereby resulting in voltage pulse V_{DS} of wide time width between drain and source terminals of MOS-FET 3. Therefore, when skip detection circuit 41 catches a first minimum voltage point of wide voltage pulse V_{DS} , MOS-FET 3 is turned on by an output from skip control circuit 42 every minimum voltage point, and normal pseudo resonance is performed by switching MOS-FET 3 from the off to the on condition at the time voltage V_{DS} between drain and source terminals of MOS-FET 3 reaches the minimum voltage point (bottom point) after flyback energy in

transformer 2 has been discharged.

Figure 16 illustrates another embodiment of control circuit 8 used in DC-DC converter of separately excited flyback type. This control circuit 8 comprises an additional or second reference power source 61, an additional or second current detection comparator 62 and a second D-flip flop 63 in parallel to first reference power source 26, first current detection comparator 27 and first D-flip flop 28. Two current detection comparators 27 and 62 compares divided voltage V_{OCP} with different reference voltages V_{DT1} and V_{DT2} of power sources 26 and 61 to control or vary occurrence cycle of pulse signal V_4 from pulse generator 22 with output signals V_{LD1} and V_{LD2} of low voltage level L respectively produced from two D-flip flops 28 and 63 under the light or very light load condition so that oscillation frequency of drive signals V_G produced from RS flip flop 23 can be lowered to different two frequencies. For example, second reference voltage V_{DT2} of second reference power source 61 can be set higher than first reference voltage V_{DT1} of first reference power source 26. In this DC-DC converter, as voltage level of detection signal V_{FB} from output detector 7 is lower than first reference voltage V_{DT1} of first power source 26 under the heavy and normal load conditions, divided voltage V_{OCP} linearly declines beneath first and second reference voltages V_{DT1} and V_{DT2} to the voltage level of detection signal V_{FB} from output detector 7. Therefore, both of first and second current detection comparators 27 and 62 produce first and second current detection signals V_{CP1} and V_{CP2} of high voltage level H. Then, when divided voltage V_{OCP} reaches voltage level of detection signal V_{FB} as shown in Figure 17(E), RS flip flop 23 changes drive signal V_G from high voltage level H to low voltage level L to gate terminal of MOS-FET 3 as shown in Figure 17(B) to turn MOS-FET 3 from on to off, reducing drain current I_D through MOS-FET 3 to

substantially zero. At this time, trailing edges shown by arrows in Figure 17(B) are given to clock input terminal CLK of first and second D-flip flops 28 and 63, and simultaneously first and second current detection comparators 27 and 62 generate first and second current detection signals V_{CP1} and V_{CP2} of high voltage level H to corresponding input terminals D of first and second D-flip flops 28 and 63 to maintain first and second signals V_{LD1} and V_{LD2} of high voltage level H from Q output terminals of first and second D-flip flops 28 and 63 as shown in Figure 17(C) and 17(D). Accordingly, under the heavy and normal load conditions, pulse generator 22 produces pulse signals V_4 of shorter cycle to shorten the off period of MOS-FET 3 and increase oscillation frequency.

When the operation moves to the light load condition, output voltage detector 7 produces detection signals V_{FB} of the voltage level higher than first reference voltage level V_{DT1} of first power source 26 but lower than second reference voltage level V_{DT2} of second power source 61, divided voltage V_{OCP} directly falls beneath second reference level V_{DT2} of second power source 61 but does not reach first reference level V_{DT1} of first power source 26. Accordingly, first current detection comparator 27 produces first current detection signals V_{CP1} of low voltage level L, but second current detection comparator 61 produces second current detection signals V_{CP2} of high voltage level H. Subsequently, when divided voltage V_{OCP} comes down to detection signal V_{FB} from output voltage detector 7 as shown in Figure 17(E), drive signals V_G is switched from high voltage level H to low voltage level L as shown in Figure 17(B) to turn MOS-FET 3 from the on to the off condition, drain current I_D through MOS-FET 3 drops to substantially zero level as shown in Figure 17(A). At the moment, trailing edge (shown by arrow) of drive signal V_G of Figure 17(B) is applied to clock input terminals CLK of D-

flip flops 28 and 63, and at the same time, first current detection signal V_{CP1} of low voltage level L from first current detection comparator 27 is furnished to input terminal D of first D-flip flop 28; second current detection signal V_{CP2} of high voltage level H from second current detection comparator 62 is furnished to input terminal D of second D-flip flop 61; first D-flip flop 28 changes signal V_{LD1} on output terminal Q from high voltage level H to low voltage level L as shown in Figure 17(C); and second D-flip flop 63 maintains high voltage level H of output signal V_{LD2} at output terminal Q as shown in Figure 17(D). Therefore, under the light load condition, pulse generator 22 produces pulse signals V_4 of longer cycle to extend the off period of MOS-FET 3, reducing oscillation frequency.

When the operation moves from the light load condition to the very light or superlight load condition not heavier than the light load condition, output voltage detector 7 produces detection signals V_{FB} of the voltage level higher than second reference voltage V_{DT2} of second power source 61 as shown in Figure 17(E), and therefore, divided voltage V_{OCP} does not drop to second reference voltage V_{DT2} of second power source 61. For that reason, both of two current detection comparators 27 and 62 produce current detection signals V_{CP1} and V_{CP2} of low voltage level L. When divided voltage V_{OCP} reaches voltage level of detection signal V_{FB} from output voltage detector 7, drive signal V_G changes from high voltage level H to low voltage level L to turn MOS-FET 3 from the on condition to the off condition as shown in Figure 17(B), reducing drain current I_D through MOS-FET 3 to substantially zero level as shown in Figure 17(A). Just then, trailing edge (shown by arrows in Figure 17(B)) of drive signal V_G is applied to clock input terminal CLK of two D-flip flops 28 and 63, and concomitantly, current detection comparators 27 and 62 supply current detection signals V_{CP1} and

V_{CP2} of low voltage level to input terminals D of D-flip flops 28 and 63 so that first D-flip flop 28 keeps signal V_{LD1} of low voltage level L on the output terminal Q as shown in Figure 17(C), while second D-flip flop 63 changes signal V_{LD2} on the output terminal Q from high voltage level H to low voltage level L. Accordingly, as pulse generator 22 under the superlight load condition produces pulse signals V_4 of the cycle longer than that under the light load condition, thereby causing further extension of the off period of MOS-FET 3 and further reduction in oscillation frequency compared with under the light load condition.

In the embodiment shown in Figure 16, as oscillation frequency of drive signal V_G to gate terminal of MOS-FET 3 can be reduced to different frequencies under the light and superlight load condition, conversion efficiency of the switching power source can be further improved by fine or stepwise control of oscillation frequency for drive signal V_G of MOS-FET 3.

Figure 18 illustrates a further DC-DC converter of separately excited flyback type according to the present invention which comprises control circuit 8 same as that shown in Figure 2 except in that control circuit of Figure 18 is provided with an intermittent oscillation controller 71 as an intermittent oscillation means for deactivating the on-off operation of MOS-FET 3 for a period of time t_B or in a cycle much longer than an oscillation cycle of drive signal V_G when D-flip flop 28 produces output signal V_{LD} of low voltage level L. The embodiment of Figure 18 utilizes a reset-priority RS flip flop 72 for preferentially producing an output on reset terminal R when input signals of high voltage level H are coincidentally applied to set and reset terminals S and R of RS flip flop 72. Receiving an output signal V_{LD} of low voltage level L from D-flip flop 28 as shown in Figure 19(C), intermittent

oscillation controller 71 produces an output signal V_5 of high voltage level H to OR gate 21 for a period of time t_B in a cycle (for example on the order of 1 to 100 milliseconds) much longer than an oscillation cycle of drive signal V_G (for example on the order of 10 to 50 microseconds) when D-flip flop 28 produces output signal V_{LD} of low voltage level L as shown in Figures 19(C) and 19(D). As OR gate 21 produces signal V_3 of high voltage level H during the period t_B of producing signal V_3 of high voltage level H from intermittent oscillation controller 71 to OR gate 21, reset-priority RS flip flop 72 retains the reset condition to supply gate terminal of MOS-FET 3 with drive signal V_G of low voltage level L for the period of time t_B . This allows change of the converter to the intermittent oscillation mode under the light load condition to keep MOS-FET 3 in the off condition during the period of time t_B in a cycle much longer than oscillation cycle of drive signal V_G .

In the DC-DC converter of separately excited flyback type shown in Figure 18, drive signals V_G shown in Figure 19 are switched to high voltage level H under the heavy and normal load conditions when pulse generator 22 provides set terminal S of reset-priority RS flip flop 72 with pulse signal V_4 to turn MOS-FET 3 on. Therefore, drain current I_D through MOS-FET 3 linearly increases as shown in Figure 19(A), and simultaneously divided voltage V_{OCP} linearly decreases under reference voltage level V_{DT} of first power source 2 so that current detection comparator 27 produces current detection signal V_{CP} of high voltage level H. And, when divided voltage V_{OCP} comes down to detection signal level V_{FB} from output voltage detector 7 as shown in Figure 19(E), drive signal V_G is changed from high voltage level H as shown in Figure 19(B) to low voltage level L to turn MOS-FET 3 from the on to the off condition, reducing drain current I_D through MOS-FET 3 to nearly zero level as shown in Figure 19(A). At this time, trailing edge of

drive signal V_G shown by arrows in Figure 19(B) is applied to clock input terminal CLK of D-flip flop 28, and coincidentally current detection comparator 27 supplies input terminal D of D-flip flop 28 with current detection signal V_{CP} of high voltage level H to maintain signal V_{LD} on output terminal Q of D-flip flop 28 on high voltage level as shown in Figure 19(C). Under the circumstances, intermittent oscillation controller 71 produces output signal V_5 of low voltage level L as shown in Figure 19(D) to cancel operation of intermittent oscillation controller 71 and thereby perform continuous usual oscillation.

Under the light load condition, output voltage detector 7 produces detection signal V_{FB} above reference voltage V_{DT} of power source 26, and therefore, divided voltage V_{OCP} does not reach reference voltage V_{DT} of power source 26 as shown in Figure 19(E), so current detection comparator 27 produces current detection signal V_{CP} of low voltage level. When divided voltage V_{OCP} falls to detection signal V_{FB} from output voltage detector 7, drive signal V_G changes from high voltage level H to low voltage level L as shown in Figure 19(A) to turn MOS-FET 3 from on to off, lowering drain current I_D through MOS-FET 3 to approximately zero level. Here, trailing edge (shown by arrows in Figure 19(B)) of drive signal V_G is input to clock input terminal CLK of D-flip flop 28, and concurrently current detection comparator 27 forwards current detection signal V_{CP} of low voltage level L to input terminal D of D-flip flop 28 which therefore switches output signal V_{LD} on output terminal Q from high voltage level H to low voltage level L to drive intermittent oscillation controller 71. Thus, as shown in Figure 19(D), intermittent oscillation controller 71 produces signal V_5 of high voltage level H during the period of time t_B in a cycle much longer than oscillation cycle of drive signal V_G , and OR gate 21 produces signal V_3 of high voltage level only

for the period t_B to send drive signal V_G of low voltage level L to gate terminal of MOS-FET 3 from reset-priority RS flip flop 72 for the period t_B . In this way, intermittent oscillation can be accomplished under the light load condition to cease the on-off operation of MOS-FET 3 for the period of time t_B in a cycle much longer than oscillation cycle for drive signals V_G .

In the embodiment shown in Figure 18, during the light load condition wherein small amount of drain current I_D flows through MOS-FET 3, D-flip flop 28 produces output signal V_{LD} of low voltage level L to switch the converter to the intermittent oscillation mode for deactivating the on-off operation of MOS-FET 3 for the period of time t_B in a cycle much longer than oscillation cycle of drive signal V_G by means of intermittent oscillation controller 71, and this allows extreme decrement of switching operation number by MOS-FET 3. Accordingly, the converter is advantageous in considerable reduction of switching loss and improvement in conversion efficiency of the switching power source in wide operation load range.

In the embodiments shown in Figures 2 to 18, DC-DC converters of separately excited flyback type demonstrate that current detection resistor 9 detects as a negative voltage electric current I_D flowing through primary winding 2a of transformer 2 or MOS-FET 3 to apply divided voltage V_{OCP} to each inverted input terminal (-) of overcurrent restricting comparator 19, current mode control comparator 20 and current detection comparator 27. Alternatively, as shown in Figure 20, current detection resistor 9 may detect as a positive voltage electric current I_D flowing through primary winding 2a of transformer 2 or MOS-FET 3 to apply the detected positive voltage directly to each non-inverted input terminal (+) of overcurrent restricting comparator 19, current mode control comparator 20 and current detection

comparator 27. In the DC-DC converter shown in Figure 20, when drive signal V_G to gate terminal of MOS-FET 3 is switched from low voltage level L to high voltage level H to turn MOS-FET 3 on, drain current I_D through MOS-FET 3 linearly increases as shown in Figure 21(A), and simultaneously detection voltage V_{OCP} on current detection resistor 9 linearly increases as shown in Figure 21(D).

Under the heavy and normal load conditions, as detection signal V_{FB} from output voltage detector 7 indicates the voltage level higher than reference voltage level V_{DT} of power source 26, detection voltage V_{OCP} on current detection resistor 9 rectilinearly increases above reference voltage level V_{DT} of power source 26 to generate current detection signal V_{CP} of high voltage level H from current detection comparator 27. Thereafter, when detection voltage V_{OCP} on current detection resistor 9 reaches detection signal V_{FB} from output voltage detector 7 as shown in Figure 21(D), drive signal V_G to gate terminal of MOS-FET 3 changes from high voltage level H to low voltage level L as shown in Figure 21 (B) to turn MOS-FET 3 from the on to the off condition, lowering drain current I_D through MOS-FET 3 to nearly zero level as shown in Figure 21(A). At this time, trailing edge of drive signal V_G of Figure 21(B) is applied to clock input terminal CLK of D-flip flop 28, and at the same time, current detection comparator 27 produces current detection signal V_{CP} of high voltage level H to input terminal D of D-flip flop 28 to keep high voltage level H of signal V_{LD} at the output terminal Q as shown in Figure 21(C). In this way, under the heavy and normal load conditions, pulse generator 22 produces pulse signal V_4 of shorter cycle to reduce the off period of MOS-FET 3, increasing oscillation frequency.

On the other hand, under the ligh load condition, since output voltage

detector 7 produces detection signal V_{FB} of voltage level lower than reference voltage level V_{DT} of power source 26, detection voltage V_{OCP} on current detection resistor 9 does not reach reference voltage level V_{DT} of power source 26, and current detection comparator 27 produces current detection signal V_{CP} of low voltage level L. When detection voltage V_{OCP} on current detection resistor 9 comes up to detection signal level V_{FB} from output voltage detector 7 as shown in Figure 21(D), drive signal V_G changes from high voltage level H to low voltage level L as shown in Figure 21(B) to turn MOS-FET 3 from the on condition to the off condition, causing drain current I_D through MOS-FET 3 to decline to approximately zero level as shown in Figure 21(A). At the moment, trailing edge (shown by arrow of Figure 21(B)) of drive signal V_G is supplied to clock input terminal CLK of D-flip flop 28, and current detection signal V_{CP} of low voltage level L from current detection comparator 27 is sent to input terminal D of D-flip flop 28 to switch signal V_{LD} from output terminal Q of D-flip flop 28 from high voltage level H to low voltage level L as shown in Figure 21(C). Accordingly, pulse generator 22 produces pulse signals V_4 of longer cycle under the light load condition to elongate the off period of MOS-FET 3 for decrement of oscillation frequency.

The embodiment shown in Figure 20 is advantageous in the simplified electric circuit due to omission of level-shifting resistors 17 and 18 from control circuit 8 shown in Figures 2 to 18. Measures for detecting switching current includes a negative detection (Figures 2 to 18) and a positive detection (Figure 20), and either of them is applicable to the present invention while they have their advantages and disadvantages.

The present invention should not be limited to any one or all of the foregoing embodiments which can be further varied in various ways as

follows:

[1] The preceding embodiments exhibit transmission of DC output voltage V_{OUT} from output rectifying smoother 6 as detection signals V_{FB} from output voltage detector 7 on the secondary side to the primary side through photo-coupler 14 of light emitting and receiving elements 14a and 14b. Unlike this, Figure 22 represents an alternative which utilizes a Zener diode 81 having the Zener voltage above drive voltage for control circuit 8 in lieu of output voltage detector 7 and photo-coupler 14 to discern detection signal V_{FB} from drive winding 2c of transformer 2 as an equivalent of DC output voltage V_{OUT} from output rectifying smoother 6. Specifically, drive winding 2c of Figure 22 produces a voltage of the proportional level to output voltage from secondary winding 2b of transformer 2, and therefore, DC voltage V_{IN} from drive winding 2c is in proportion to DC output voltage V_{OUT} on secondary winding 2b. In this way, since drive winding 2c enables to detect change in DC output voltage V_{OUT} on secondary winding 2b, the converter shown in Figure 22 does need neither output voltage detector 7 nor photo-coupler 14, achieving the simplified circuitry on the secondary side.

[2] The above-described embodiments display detection as a negative or positive voltage of electric current I_D flowing through primary winding 2a of transformer 2 or MOS-FET 3 by means of current detecting resistor 9 connected in series to primary winding 2a or MOS-FET 3. Instead, Figure 23 contemplates utilization of a switching element which comprises a sense MOS-FET 91 having a current detection terminal 92 as a shunt for dividing electric current I_D flowing through a closed circuit inclusive of primary winding 2a of transformer 2 to convert electric current passing through current detection terminal 92 into a corresponding voltage with

current detection resistor 9.

[3] Figure 9 illustrates the converter which comprises double series stage D-flip flops 50 and 51 for turning MOS-FET 3 on at the second minimum point of voltage between drain and source terminals of MOS-FET 3 during the light load condition, however, the converter may comprise three or more series stage D-flip flops for turning MOS-FET 3 on at the third or every third or more minimum point of voltage between drain and source terminals of MOS-FET 3 during the light load condition. This arrangement allows further decrease in oscillation frequency of drive signals V_G applied to gate terminal of MOS-FET 3 to achieve further reduction of switching loss under the light load condition.

[4] Similarly to the embodiment shown in Figure 16, control circuit 8 may comprise three sets of power sources 26, current detection comparators 27 and D-flip flops 28 to more finely control oscillation frequency of drive signals V_G to gate terminal of MOS-FET 3 under the light load condition in response to the load state.

[5] Also, as shown in Figure 24, the converter of Figure 16 may comprise bottom detection circuit 41 and skip control circuit 42 shown in Figure 9. Specifically, DC-DC converter of separately excited flyback type shown in Figure 24 comprises control circuit 8 which is provided with bottom detection circuit 41 and skip control circuit 42. Bottom detection circuit 41 serves to discern minimum points of voltage V_{DS} between drain and source terminals of MOS-FET 3 in the light of ringing voltages produced on drive winding 2c of transformer 2 during the off period of MOS-FET 3. Skip control circuit 42 functions to firstly turn MOS-FET 3 on at the first minimum point

of voltage V_{DS} discerned by bottom detection circuit 41 when both of D-flip flops 28 and 63 produce output signals V_{LD1} and V_{LD2} of high voltage level H, secondly turn MOS-FET 3 on at the second minimum point of voltage V_{DS} discerned by bottom detection circuit 41 when first and second D-flip flops 28 and 63 produce output signals V_{LD1} and V_{LD2} of respectively low voltage level L and high voltage level H; and thirdly turn MOS-FET 3 on at the third minimum point of voltage V_{DS} discerned by bottom detection circuit 41 when both of first and second D-flip flops 28 and 63 produce output signals V_{LD1} and V_{LD2} of low voltage level L. Skip control circuit 42 shown in Figure 24 comprises third, fourth and fifth D-flip flops 50, 51 and 54 connected in series; a first AND gate 52 for outputting logical product signal V_{AD1} of output signal V_{DF1} from third D-flip flop 50 and output signal V_{LD1} from first D-flip flop 28; a second AND gate 55 for outputting logical product signal V_{AD2} of output signal V_{DF2} from fourth D-flip flop 51 and output signal V_{LD2} from second D-flip flop 63; and an OR gate 53 for outputting logical sum signal V_{OR} of pulse signal V_4 from pulse generator 22, output signal V_{DF3} from fifth D-flip flop 54, logical product signal V_{AD1} from first AND gate 52, and logical product signal V_{AD2} from second AND gate 55. In other words, as both of D-flip flops 28 and 63 of skip control circuit 42 shown in Figure 24, produce output signals V_{LD1} and V_{LD2} of high voltage level H under the heavy and normal load conditions as shown in Figures 25(D) and 25(E), logical product signals V_{AD1} and V_{AD2} from first and second AND gates 52 and 55 are respectively the same as output signals V_{DF1} and V_{DF2} from third and fourth D-flip flops 50 and 51. On the other hand, as third D-flip flop 50 produces a single pulsative output signal V_{DF1} of high voltage level synchronously with initial rising edge of output signal V_{BD} from bottom detection circuit 41 shown in Figure 25(C), fourth and fifth D-flip flops 51 and 54 maintain output signals V_{DF2} and V_{DF3} of low voltage level L. Accordingly, as OR gate 53

produces a single pulsatile logical sum signal V_{OR} of high voltage level H in synchronization with initial rising edge of output signal V_{BD} from bottom detection circuit 41, MOS-FET 3 can be turned on at the first minimum voltage point perceived by bottom detection circuit 41 under the heavy and normal load conditions. Also, under the light load condition, first and second D-flip flops 28 and 63 produce respectively output signal V_{LD1} of low voltage level L and output signal V_{LD2} of high voltage level H so that first AND gate 52 generates logical product signal V_{AD1} of low voltage level L. On the other hand, fourth D-flip flop 51 produces a single pulsatile output signal V_{DF2} of high voltage level H synchronously with a second trailing edge of output signal V_{BD} from bottom detection circuit 41 shown in Figure 25(C), and therefore, second AND gate 55 produces logical product signals V_{AD2} same as output signal V_{DF2} so that OR gate 53 produces a single pulsative logical sum signal V_{OR} of high voltage level H coincidentally with a second trailing edge of output signal V_{BD} from bottom detection circuit 41. In this way, MOS-FET 3 can be turned on at the second minimum voltage point descerned by bottom detection circuit 41 under the light load condition, Moreover, as both of D-flip flops 28 and 63 produce output signals V_{LD1} and V_{LD2} of low voltage level L under the superlight load condition as shown in Figures 25(D) and 25(E), both of first and second AND gates 52 and 55 produce logical product signals V_{AD1} and V_{AD2} of low voltage level L. However, because fifth D-flip flop 54 produces a single pulsatile signal V_{DF3} of high voltage level synchronously with a third trailing edge of output signal V_{BD} from bottom detection circuit 41 shown in Figure 25(C), OR gate 53 produces a single pulsatile logical sum signal V_{OR} of high voltage level H concurrently with a third trailing edge of output signal V_{BD} from bottom detection circuit 41. In this way, MOS-FET 3 can be turned on at the third minimum voltage point picked out by bottom detection circuit 41 under the superlight load condition. Accordingly,

similarly to the embodiment shown in Figure 16, the embodiment shown in Figure 24 also can achieve reduction of oscillation frequency to different two frequencies of drive signal V_G applied to gate terminal to MOS-FET 3 as shown in Figure 25(B) under the light and superlight load conditions to more finely control oscillation frequency of drive signal V_G of MOS-FET 3 for further enhancement of conversion efficiency in switching power source. Still further modifications can of course be made such as provision of three sets of reference power sources 26, current detection comparators 27 and D-flip flops 28 connected in parallel to each other, or provision of series four or more stage of D-flip flops 50 to reduce oscillation frequency of drive signal V_G to different three or more frequencies in the light of load degrees.

[6] The foregoing embodiments of the invention offer converters of the type for controlling separately the on and off periods MOS-FET 3; and the type for controlling pseudo resonance in ringing choke converter. However, the present invention can also be applied to converters of general pulse width modulation type for controlling on-duty or on-period of MOS-FET.

[7] Moreover, the present invention can also be applied other switching power sources such as resonance type or separately excited forward type connected to DC power source or with power source for providing control circuit with electric power, without limitation to DC-DC converters of separately excited flyback type.

The switching power source according to the present invention, is advantageous because it is immune from foreign noise such as induction noise and load condition on the secondary side can precisely and certainly be detected on the primary side with minimum number of required components

because the load condition on the secondary side is examined at the swiching point of turning a switching element from the on condition to the off condition. Accordingly, shift to an optimal oscillation operation in the switching power source based on detection output of the load condition enables improvement in conversion efficiency.

INDUSTRIAL APPLICABILITY

The present invention can be applied to AC adoptors for electronic devices such as portable personal computers, mobile phones or personal handyphone systems provided with large scale public addressor such as microcomputer.